

STB60N55F3, STD60N55F3, STF60N55F3 STI60N55F3, STP60N55F3, STU60N55F3

N-channel 55 V, 6.5 mΩ 80 A, DPAK, IPAK, D²PAK, I²PAK, TO-220 TO-220FP STripFET™ III Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)}	I _D	Pw
STB60N55F3	55V	$<$ 8.5m Ω	80A	110W
STD60N55F3	55V	<8.5mΩ	80A	110W
STF60N55F3	55V	<8.5mΩ	42A	30W
STI60N55F3	55V	<8.5mΩ	80A	110W
STP60N55F3	55V	<8.5mΩ	80A	110W
STU60N55F3	55V	<8.5mΩ	80A	110W

- Standard threshold drive
- 100% avalanche tested

Application

■ Switching applications

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performances.

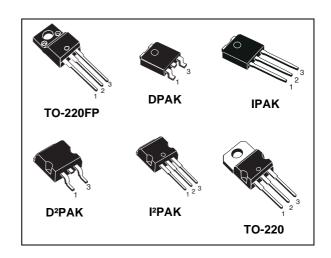


Figure 1. Internal schematic diagram

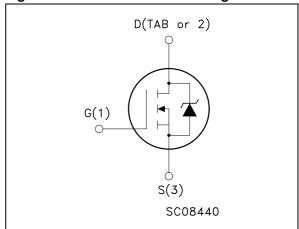


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB60N55F3	60N55F3	D²PAK	Tape and reel
STD60N55F3	60N55F3	DPAK	Tape and reel
STF60N55F3	60N55F3	TO-220FP	Tube
STI60N55F3	60N55F3	I ² PAK	Tube
STP60N55F3	60N55F3	TO-220	Tube
STU60N55F3	60N55F3	IPAK	Tube

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STx60N55F3 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

		Valu	e	
Symbol	Symbol Parameter		TO-220FP	Unit
V _{DS}	Drain-source voltage (V _{GS} =0)	55		V
V _{GS}	Gate-source voltage	± 20)	V
I _D	Drain current (continuous) at T _C = 25°C	42	Α	
I _D	Drain current (continuous) at T _C = 100°C	56	30	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	320	168	Α
P _{TOT}	Total dissipation at T _C = 25°C	110	30	W
	Derating factor	0.73	0.2	W/°C
dv/dt ⁽²⁾	Peak diode recovery voltage slope	11		V/ns
E _{AS} (3)	Single pulse avalanche energy	390		mJ
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T _C =25°C)		V	
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 175		°C

^{1.} Pulse width limited by safe operating area

Table 3. Thermal resistance

		Value					
Symbol	Parameter	DPAK	IPAK I²PAK	D²PAK	TO-220	TO-220FP	Unit
Rthj-case	Thermal resistance junction- case max	1.36			5	°C/W	
Rthj-pcb (1)	Thermal resistance junction- pcb max	50		35			°C/W
Rthj-a	Thermal resistance junction- ambient max		100		62.5		°C/W
Tı	Maximum lead temperature for soldering purpose	275 3		300	°C		

^{1.} When mounted on FR-4 board of 1inch², 2oz Cu



^{2.} $I_{SD} \le 80 \text{ A, di/dt} \le 300 \text{A/µs, } V_{DD} \le V_{(BR)DSS.} \text{Tj} \le Tjmax$

^{3.} Starting Tj=25°C, Id=32 A, Vdd= 25 V

Electrical characteristics STx60N55F3

2 Electrical characteristics

(T_{CASE}= 25 °C unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	55			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating, Tc = 125°C			10 100	μ Α μ Α
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20V			±200	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	٧
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 32A		6.5	8.5	mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} =25V, I _D =32A	-	50		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V$, $f = 1MHz$, $V_{GS} = 0$	-	2200 500 25		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 27V, I_D = 65A V_{GS} =10V (see Figure 16)	-	33.5 12.5 9.5	45	nC nC nC

^{1.} Pulsed: pulse duration = 300 μ s, duty cycle 1.5%

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r	Turn-on delay time Rise time	V_{DD} = 27V, I_D = 32A, R_G = 4.7 Ω , V_{GS} = 10V (see Figure 18)	-	20 50	-	ns ns
t _{d(off)}	Turn-off delay time Fall time	$V_{DD} = 27V$, $I_D = 32A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 18)	-	35 11.5	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Packages	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)		DPAK-D ² PAK- I ² PAK-I ² PAK- TO-220	-		80 320	A A
I _{SD}	Source-drain current Source-drain current (pulsed)		TO-220FP	-		42 168	A A
V _{SD}	Forward on voltage	$I_{SD} = 65A, V_{GS} = 0$		-		1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 65A$, $V_{DD} = 30V$ di/dt = 100A/ μ s, Tj = 150°C (see Figure 17)		-	47 87 3.7		ns nC A

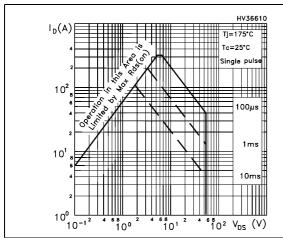
^{1.} Pulsed: pulse duration = 300 μ s, duty cycle 1.5%

Electrical characteristics STx60N55F3

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 D2PAK / IPAK / I2PAK / DPAK

Figure 3. Thermal impedance for TO-220 D2PAK / IPAK / IPAK / DPAK



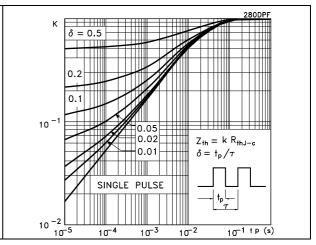
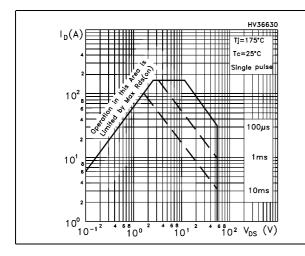


Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP



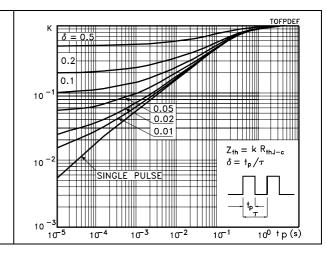
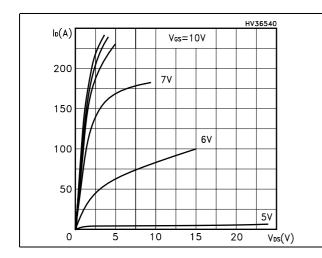


Figure 6. Output characteristics

Figure 7. Transfer characteristics



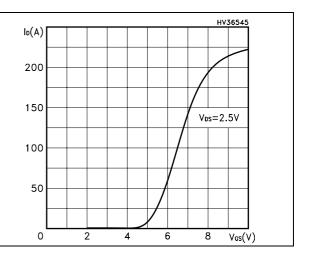
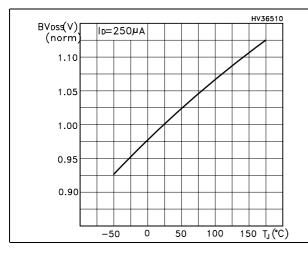


Figure 8. Normalized BV_{DSS} vs temperature

Figure 9. Static drain-source on resistance



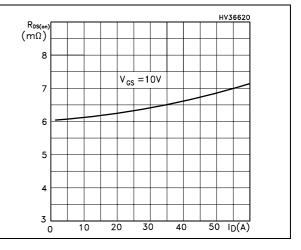
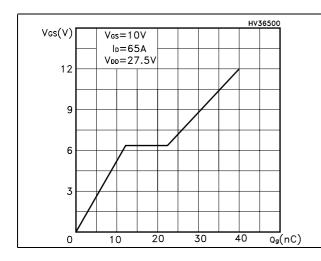
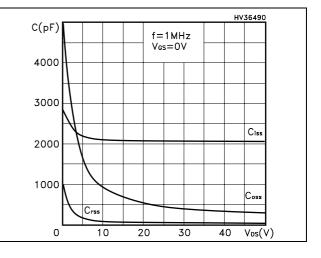


Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations





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Electrical characteristics STx60N55F3

Figure 12. Normalized gate threshold voltage Figure 13. Normalized on resistance vs vs temperature temperature

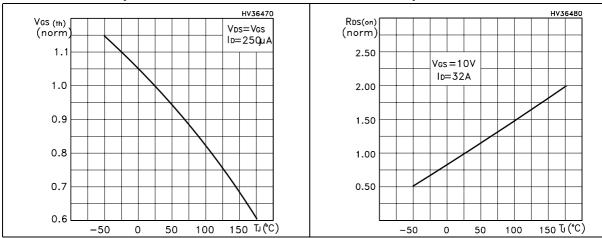
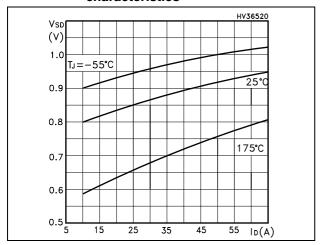


Figure 14. Source-drain diode forward characteristics



STx60N55F3 Test circuits

3 Test circuits

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

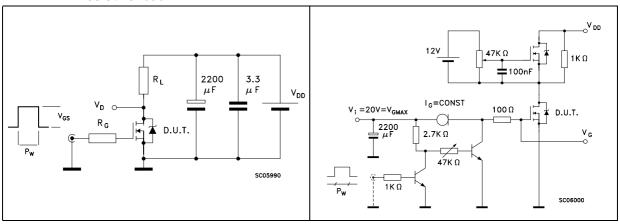


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped inductive load test circuit

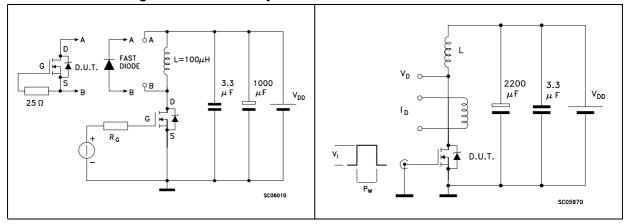
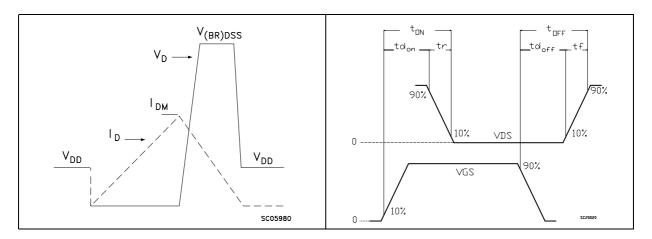


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform



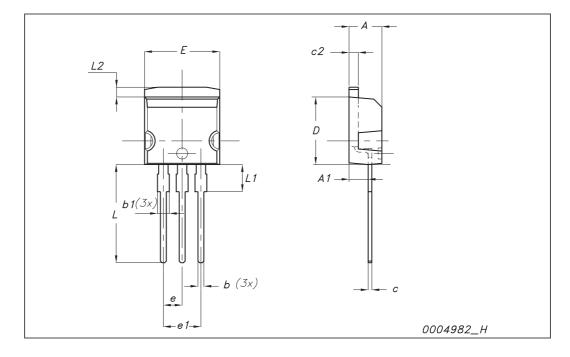
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Package mechanical data 4

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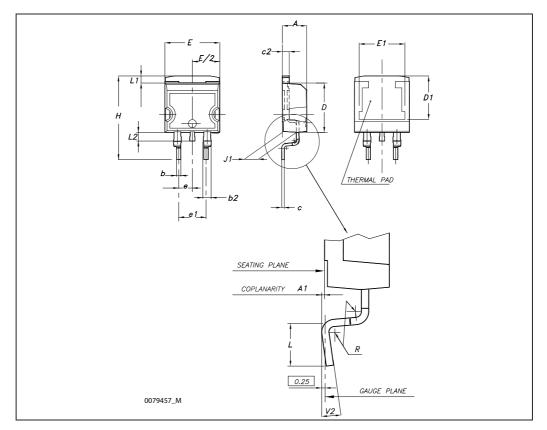
I²PAK (TO-262) mechanical data

Dim	mm			inch		
Dilli	Min	Тур	Max	Min	Тур	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



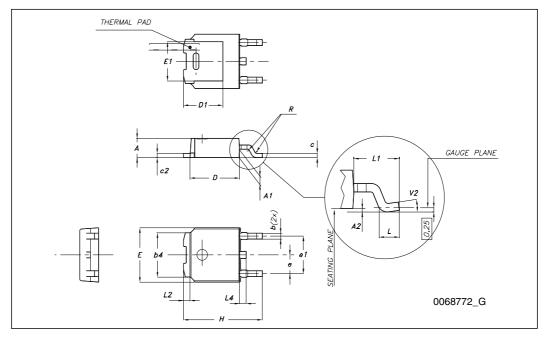
D²PAK (TO-263) mechanical data

D:		mm			inch			
Dim	Min	Тур	Max	Min	Тур	Max		
Α	4.40		4.60	0.173		0.181		
A1	0.03		0.23	0.001		0.009		
b	0.70		0.93	0.027		0.037		
b2	1.14		1.70	0.045		0.067		
С	0.45		0.60	0.017		0.024		
c2	1.23		1.36	0.048		0.053		
D	8.95		9.35	0.352		0.368		
D1	7.50			0.295				
E	10		10.40	0.394		0.409		
E1	8.50			0.334				
е		2.54			0.1			
e1	4.88		5.28	0.192		0.208		
Н	15		15.85	0.590		0.624		
J1	2.49		2.69	0.099		0.106		
L	2.29		2.79	0.090		0.110		
L1	1.27		1.40	0.05		0.055		
L2	1.30		1.75	0.051		0.069		
R		0.4			0.016			
V2	0°		8°	0°		8°		



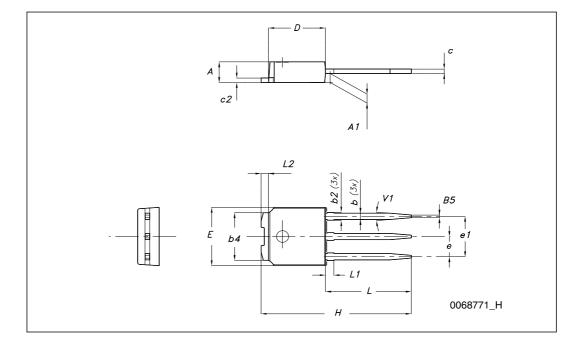
TO-252 (DPAK) mechanical data

DIM.		mm.	
DIWI.	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
е		2.28	
e1	4.40		4.60
Н	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



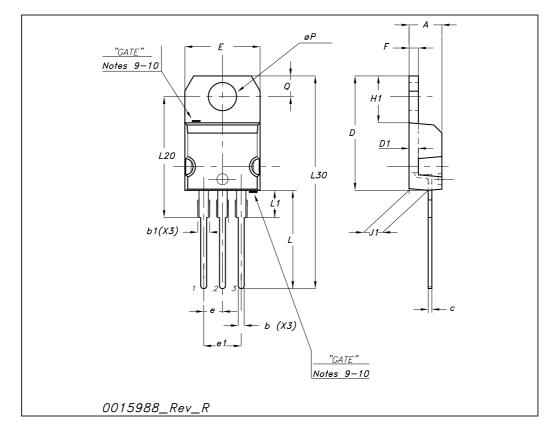
TO-251 ((IPAK)	mechanical	data
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DIM.	mm.				
	min.	typ	max.		
А	2.20		2.40		
A1	0.90		1.10		
b	0.64		0.90		
b2			0.95		
b4	5.20		5.40		
С	0.45		0.60		
c2	0.48		0.60		
D	6.00		6.20		
E	6.40		6.60		
е		2.28			
e1	4.40		4.60		
Н		16.10			
L	9.00		9.40		
(L1)	0.80		1.20		
L2		0.80			
V1		10 °			



TO-220 mechanical data

Dim		mm		inch		
	Min	Тур	Max	Min	Тур	Max
А	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

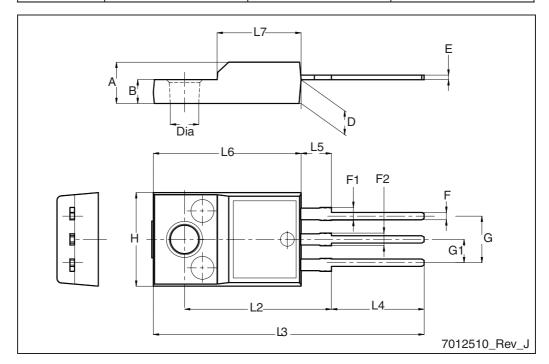


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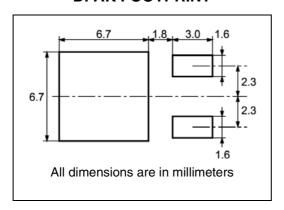
TO-220FP mechanical data

Dim.	mm				
	Min.	Тур.	Max.		
А	4.4		4.6		
В	2.5		2.7		
D	2.5		2.75		
E	0.45		0.7		
F	0.75		1		
F1	1.15		1.70		
F2	1.15		1.5		
G	4.95		5.2		
G1	2.4		2.7		
Н	10		10.4		
L2		16			
L3	28.6		30.6		
L4	9.8		10.6		
L5	2.9		3.6		
L6	15.9		16.4		
L7	9		9.3		
Dia	3		3.2		

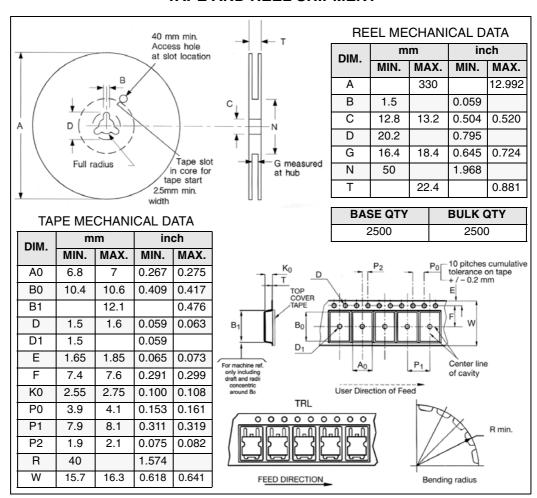


5 Packaging mechanical data

DPAK FOOTPRINT



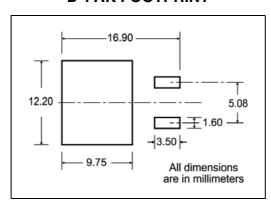
TAPE AND REEL SHIPMENT



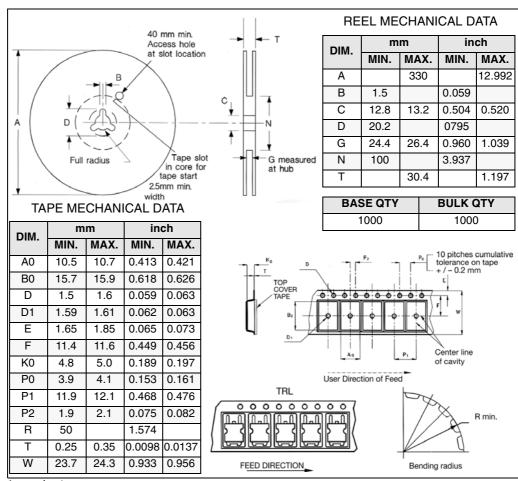


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D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

STx60N55F3 Revision history

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
09-Feb-2007	1	First release
22-Feb-2007	2	Description has been updated
07-Mar-2007	3	The Figure 2, Figure 4, Figure 9 have been changed
17-Apr-2009	4	Added device in I ² PAK Updated all mechanical data

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